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Octopus II

The OCTOPUS platform makes double sided deposition easy and provides consistently high film quality. Ideal for heterojunction cell development, MEMS manufacture or opto-electronic layers.

- > Very flexible system concept for thin film deposition
- Excellent film thickness uniformity
- Excellent film passivation levels

> PECVD, PVD layers, or combinations in the same system

> PECVD: extremely stable plasma ignition, even at low power (<10 mW/cm²), low bombardment

> R&D and pilot production

> Substrate size: 350 x 450 mm max. or 4 wafers per 6 inch

- Small footprint: LxWxH 2.5 x 2.5 x 1.7 meters (PECVD)
- > High throughput possible: > 1.3 Mio wafers (6") p.a.
- Fully automated system and process control
- > User-friendly GUI
- Process & system data logging

CUSTOMIZED MODULE_

> LPCVD, Hot wire, etching modules

PVD

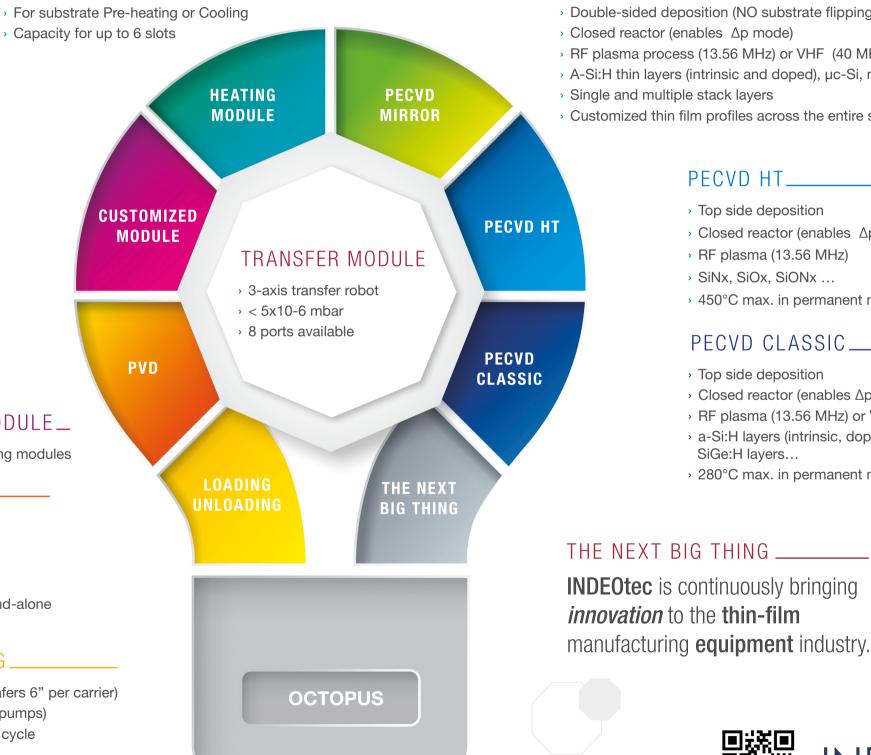
- > 3 top, 3 bottom cathode ports (planar or rotary)
- > Power type: DC, pulsed DC, RF
- With separate Loading/Unloading
- Adjustable target-substrate distance
- > Options: port-connected to OCTOPUS II or as Stand-alone

LOADING / UNLOADING _____

- > 6 substrate or carrier slots (4 wafers 6" per carrier)
- Pumping/Venting station (turbo pumps)
- High-throughput per deposition cycle
- Substrate auto-tracking



HEATING MODULE _____



 Double-sided deposition (NO substrate flipping necessary) > RF plasma process (13.56 MHz) or VHF (40 MHz) > A-Si:H thin layers (intrinsic and doped), µc-Si, mc-Si layers

Customized thin film profiles across the entire surface

PECVD HT

PECVD MIRBOR

Top side deposition Closed reactor (enables \Delta p mode) > RF plasma (13.56 MHz) > SiNx, SiOx, SiONx ... > 450°C max. in permanent mode

PECVD CLASSIC

Top side deposition Closed reactor (enables ∆p mode) > RF plasma (13.56 MHz) or VHF (40 MHz) > a-Si:H layers (intrinsic, doped), µc-Si, mc-Si, SiGe:H layers... > 280°C max. in permanent mode

